SG2M021120B

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2

Features

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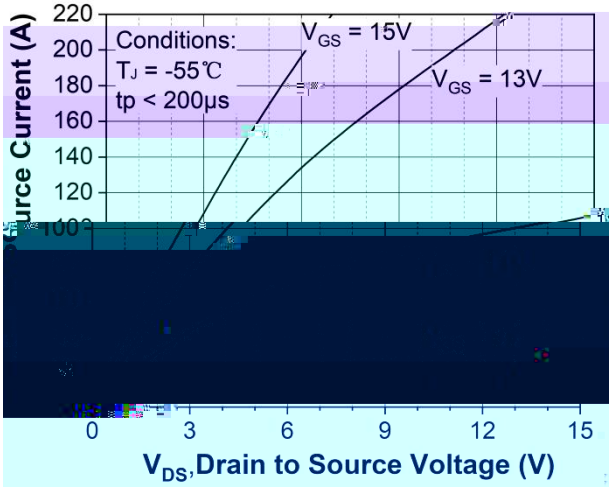
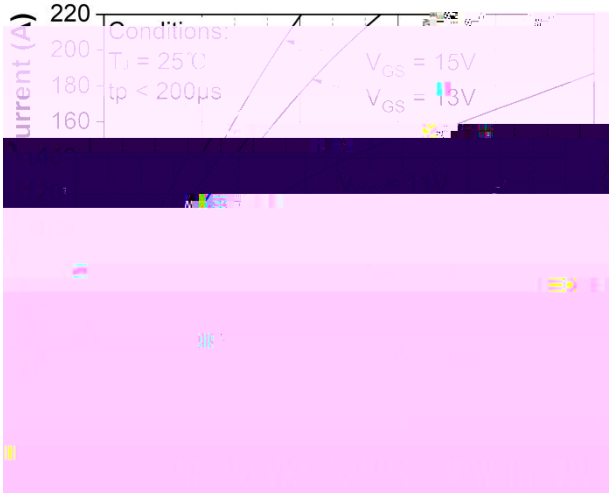
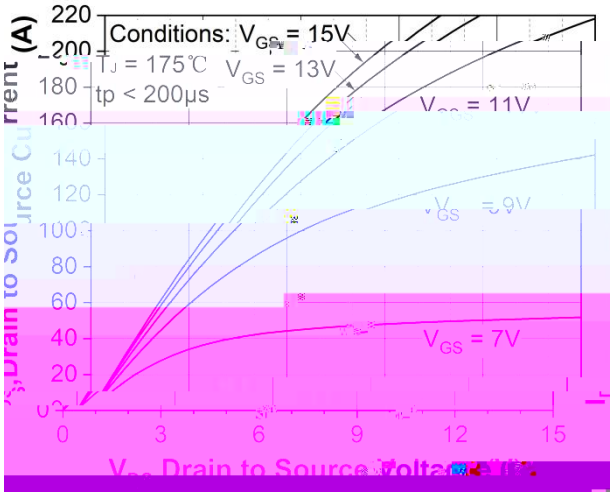
3.3 Switching characteristics

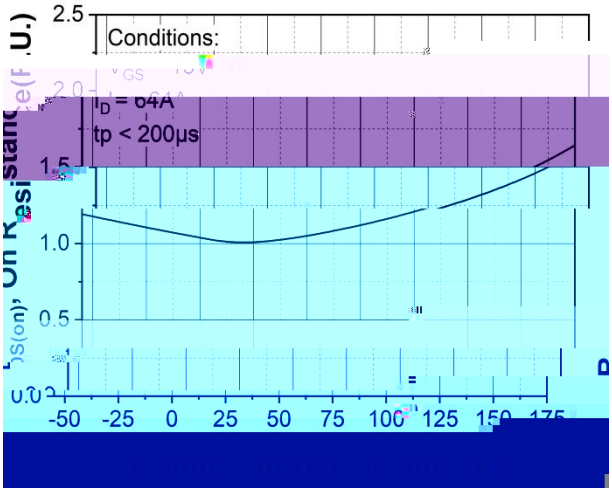
Table 6 Dynamic characteristics

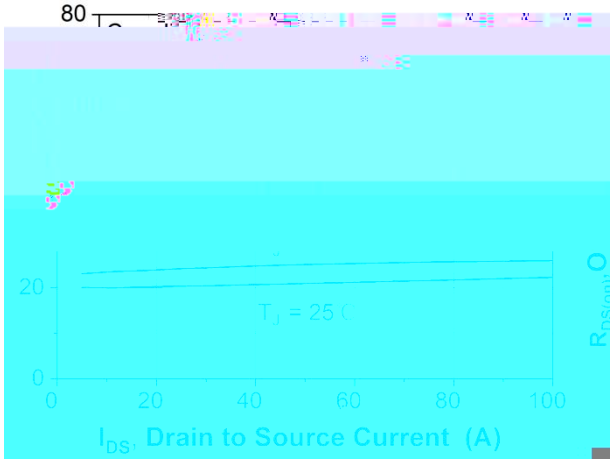
4 Electrical characteristic diagrams

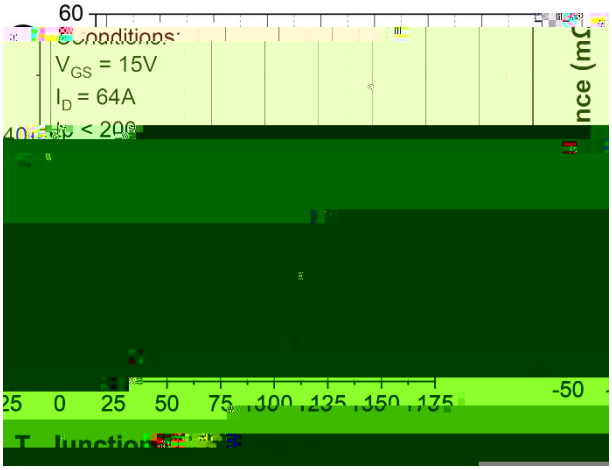












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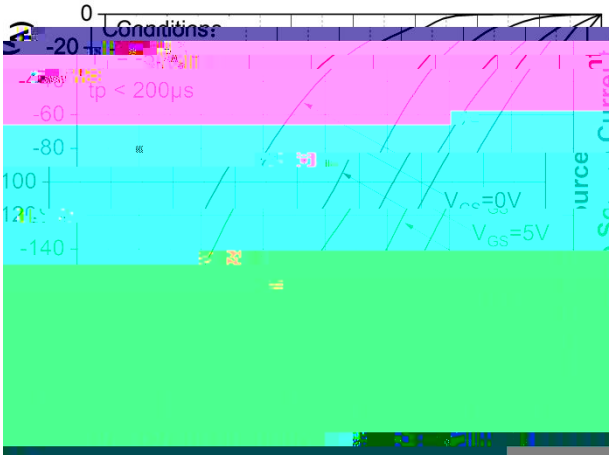
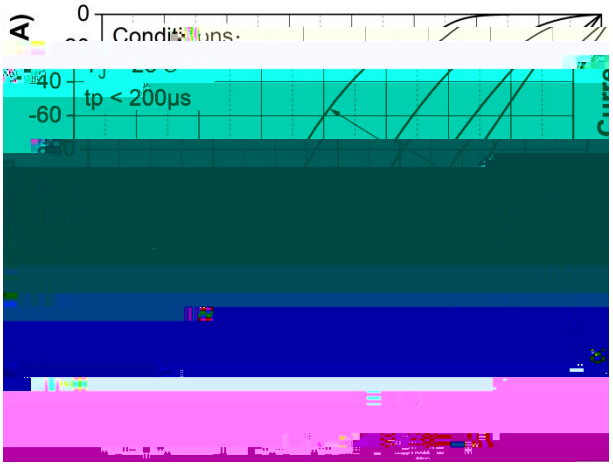
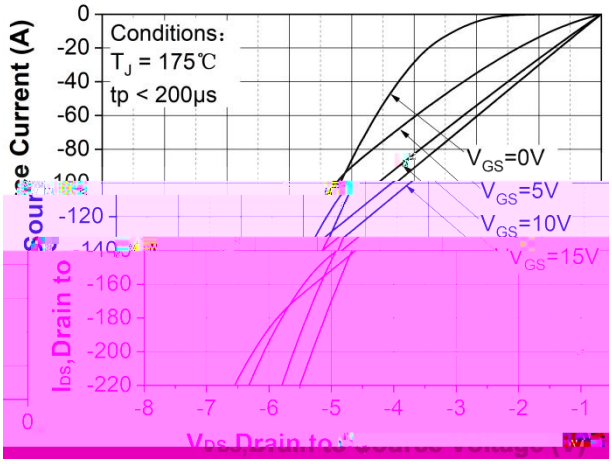
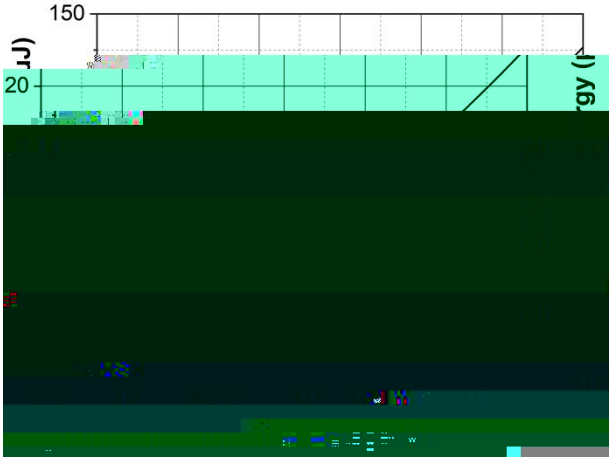
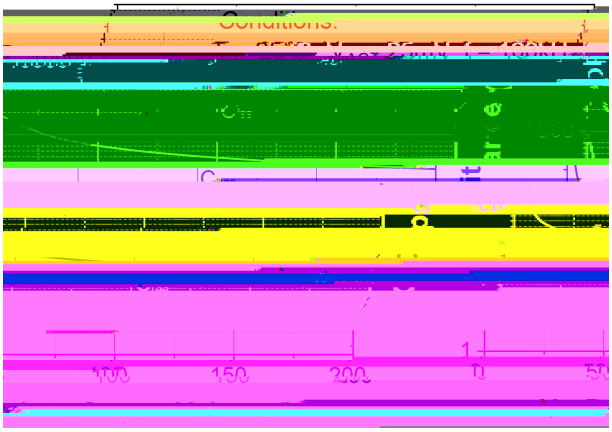
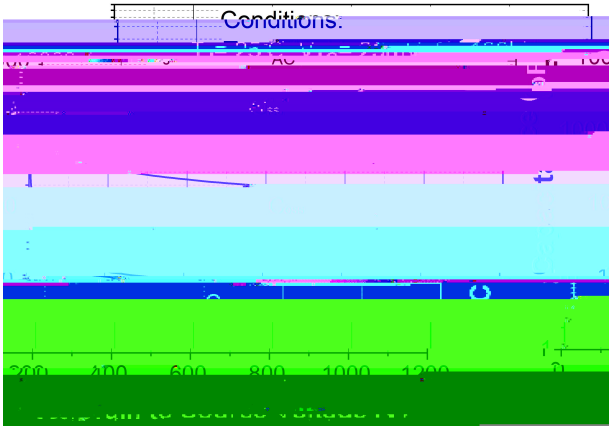

Conditions:
tp < 200μs
VGS=0V
VGS=5V


tp < 200μs


Conditions:
TJ = 175℃
tp < 200μs
VGS=0V
VGS=5V
VGS=10V
VGS=15V
Drain to
Drain to





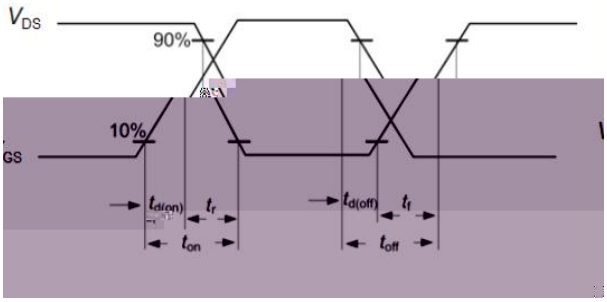

Conditions:

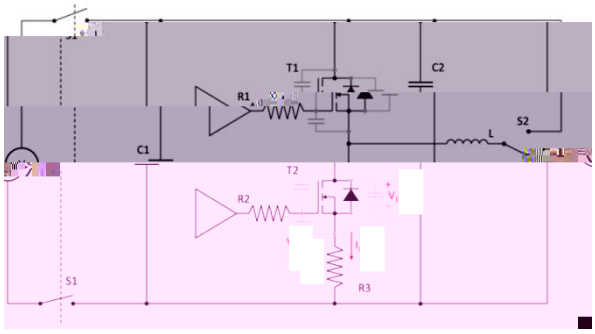
4 Mechanical parameters

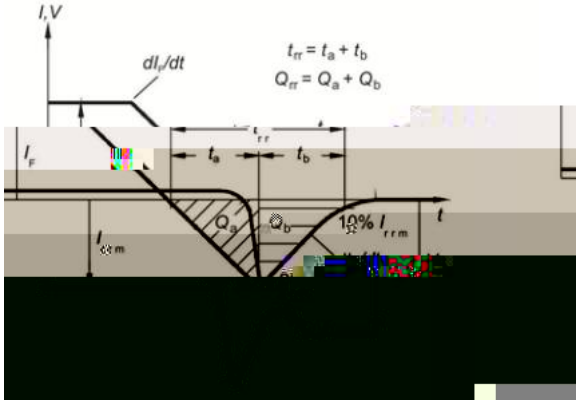
4.1 Dimensions and metallization

Parameter	Typical value	Unit	Metallization

5 Test conditions







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1200V SiC Power MOSFET

Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2025-08-08		
V01_01	2025-12-25	Final	

Attention

RoHS compliance

REACH compliance

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